



SPT25N135F1A

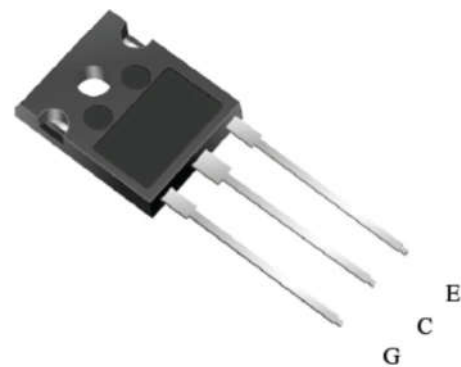
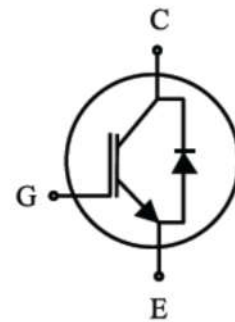
1350V /25A Trench Field Stop IGBT

Field Stop Trench IGBTs offer low switching losses, high energy efficiency and high avalanche ruggedness for soft switching applications such as inductive heating, microwave oven, etc.

| | | |
|-----------------------|------|---|
| V_{CE} | 1350 | V |
| I_C | 25 | A |
| $V_{CE(SAT)} I_C=25A$ | 2.0 | V |

FEATURES

- High breakdown voltage to 1350V for improved reliability
- Trench-Stop Technology offering :
 - High speed switching
 - High ruggedness, temperature stable
 - Low V_{CEsat}
 - Easy parallel switching capability due to positive temperature coefficient in V_{CEsat}
- Soft current turn-off waveforms
- Enhanced avalanche capability



APPLICATION

- Inductive cooking
- Inverterized microwave ovens
- Resonant converters
- Soft switching applications



Maximum Ratings

| Parameter | Symbol | Value | Unit |
|---|-------------|------------|------------------|
| Collector-Emitter Breakdown Voltage | V_{CE} | 1350 | V |
| DC collector current, limited by T_{jmax} $T_C = 25^\circ\text{C}$ $T_C = 100^\circ\text{C}$ | I_C | 50 25 | A |
| Diode Forward current, limited by T_{jmax} $T_C = 25^\circ\text{C}$ $T_C = 100^\circ\text{C}$ | I_F | 50 25 | A |
| Pulsed collector current, t_p limited by T_{jmax} | I_{Cpuls} | 75 | A |
| Turn off safe operating area $V_{CE} \leq 1350\text{V}$, $T_j \leq 150^\circ\text{C}$ | - | 75 | A |
| Operating junction temperature T_j | - | -40...+150 | $^\circ\text{C}$ |
| Storage temperature | T_s | -55...+150 | $^\circ\text{C}$ |
| Soldering temperature, wave soldering 1.6mm (0.063in.) from case for 10s | - | 260 | $^\circ\text{C}$ |

Thermal Resistance

| Parameter | Symbol | Max. Value | Unit |
|--|-------------------|------------|------|
| IGBT thermal resistance, junction - case | $R_{\theta(j-c)}$ | 0.48 | K/W |
| Diode thermal resistance, junction - case | $R_{\theta(j-c)}$ | 1.2 | K/W |
| Thermal resistance, junction - ambient | $R_{\theta(j-a)}$ | 40 | K/W |

**Electrical Characteristics of the IGBT** ($T_j = 25^\circ\text{C}$ unless otherwise specified) :

| Parameter | Symbol | Conditions | Min | Typ | Max | Unit |
|--------------------------------------|---------------|--|--------|---------|-------------|---------|
| Static | | | | | | |
| Collector-Emitter breakdown voltage | BV_{CES} | $V_{GE}=0V, I_C=1mA$ | 1350 | 1450 | - | V |
| | | $V_{GE}=0V, I_C=10mA$ | 1350 | 1450 | - | V |
| Gate threshold voltage | $V_{GE(th)}$ | $V_{GE}=V_{CE}, I_C=250\mu A$ | 5.1 | 5.8 | 6.4 | V |
| Collector-Emitter Saturation voltage | $V_{CE(sat)}$ | $V_{GE}=15V, I_C=25A$ | - | 2.0 | 2.5 | V |
| | | $T_j = 150^\circ\text{C}$ | - | 2.5 | - | |
| Zero gate voltage collector current | I_{CES} | $V_{CE} = 1350V, V_{GE} = 0V$ $T_j = 25^\circ\text{C}$ $T_j = 150^\circ\text{C}$ | - - | <1 - | 100 1000 | μA |
| Gate-emitter leakage current | I_{GES} | $V_{CE} = 0V, V_{GE} = 20V$ | - | - | 100 | nA |

| Parameter | Symbol | Conditions | Min | Typ | Max | Unit |
|------------------------------|-----------|---|-----|------|-----|------|
| Dynamic | | | | | | |
| Input capacitance | C_{ies} | $V_{CE} = 25V, V_{GE} = 0V,$ $f = 1MHz$ | - | 2500 | - | pF |
| Output capacitance | C_{oes} | | - | 70 | - | |
| Reverse transfer capacitance | C_{res} | | - | 50 | - | |
| Gate charge | Q_G | $V_{CC} = 600V, I_C = 25A,$ $V_{GE} = 15V$ | - | 125 | - | nC |

Switching Characteristic, Inductive Load

| Parameter | Symbol | Conditions | Min | Typ | Max | Unit |
|--|--------------|--|-----|------|-----|------|
| Dynamic , at $T_j = 25^\circ\text{C}$ | | | | | | |
| Turn-off delay time | $td_{(off)}$ | $V_{CC} = 600V, I_C = 25A,$ $V_{GE} = 0/15V,$ $R_g=10\Omega$ | - | 180 | - | ns |
| Fall time | t_f | | - | 40 | - | ns |
| Turn-off energy | E_{off} | | - | 0.32 | - | mJ |
| Dynamic , at $T_j = 150^\circ\text{C}$ | | | | | | |
| Turn-off delay time | $td_{(off)}$ | $V_{CC} = 600V, I_C = 25A,$ $V_{GE} = 0/15V,$ $R_g=10\Omega$ | - | 220 | - | ns |
| Fall time | t_f | | - | 90 | - | ns |
| Turn-off energy | E_{off} | | - | 0.65 | - | mJ |



Electrical Characteristics of the DIODE ($T_j = 25^\circ\text{C}$ unless otherwise specified)

| Parameter | Symbol | Conditions | Min | Typ | Max | Unit |
|--------------------------|----------|--|-----|------|-----|------|
| Dynamic | | | | | | |
| Diode Forward Voltage | V_{FM} | $I_F = 25\text{A}$ | - | 2.3 | - | V |
| Reverse Recovery Time | T_{rr} | $I_F = 25\text{A},$ $di/dt = 200\text{A}/\mu\text{s}$ | - | 460 | - | ns |
| Reverse Recovery Current | I_{rr} | | - | 17 | - | A |
| Reverse Recovery Charge | Q_{rr} | | - | 3600 | - | nC |



Fig. 1 FBSOA characteristics

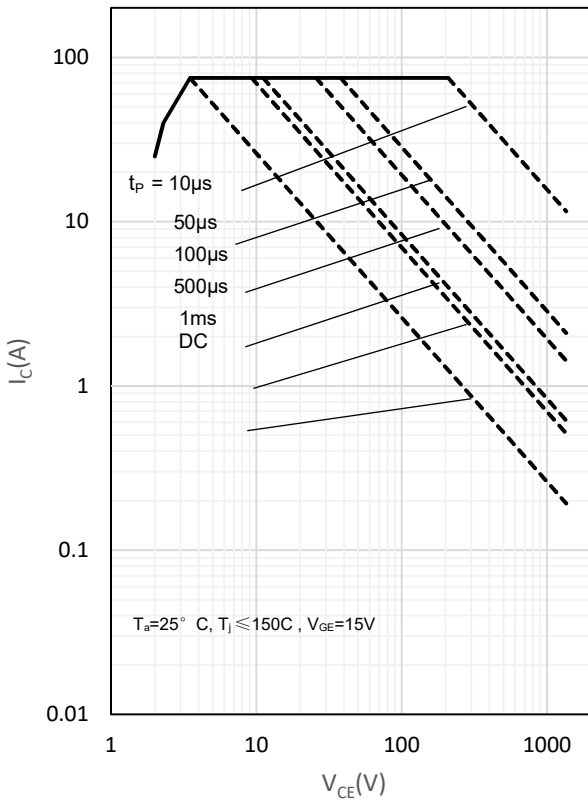


Fig. 2 Load Current vs. Frequency

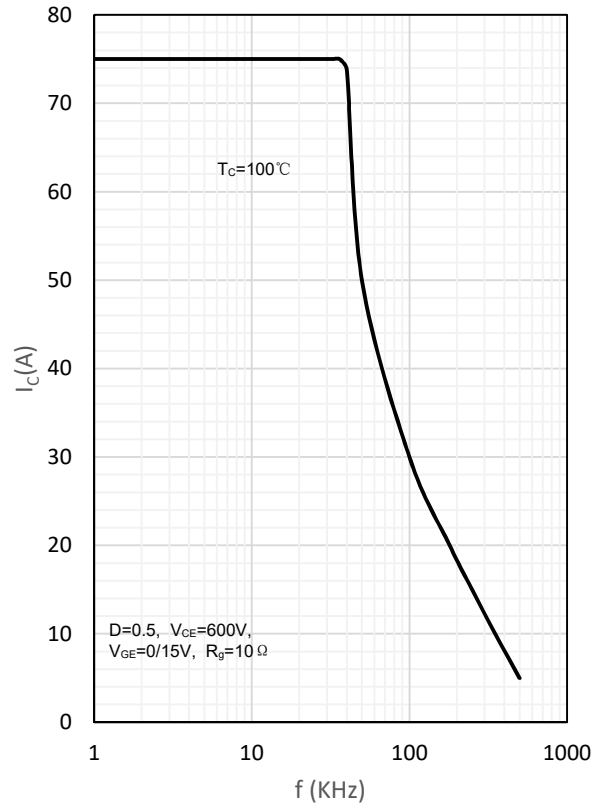


Fig. 3 Output characteristics

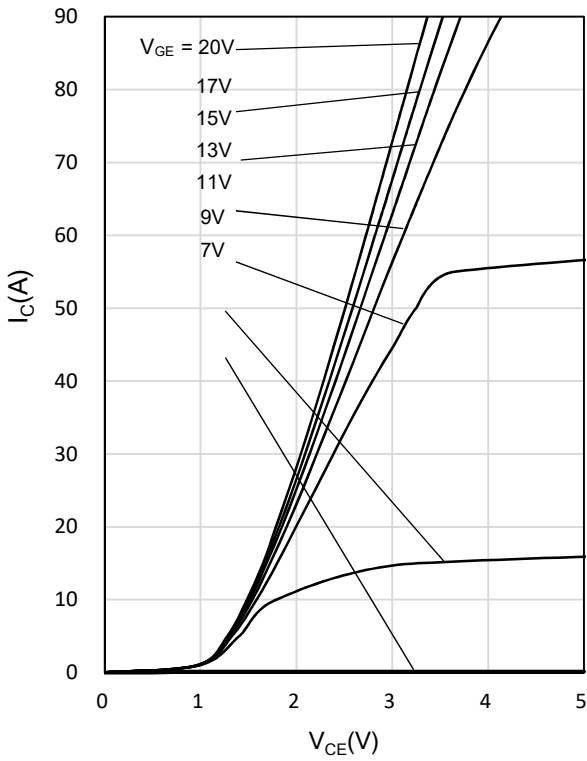


Fig. 4 Saturation voltage characteristics

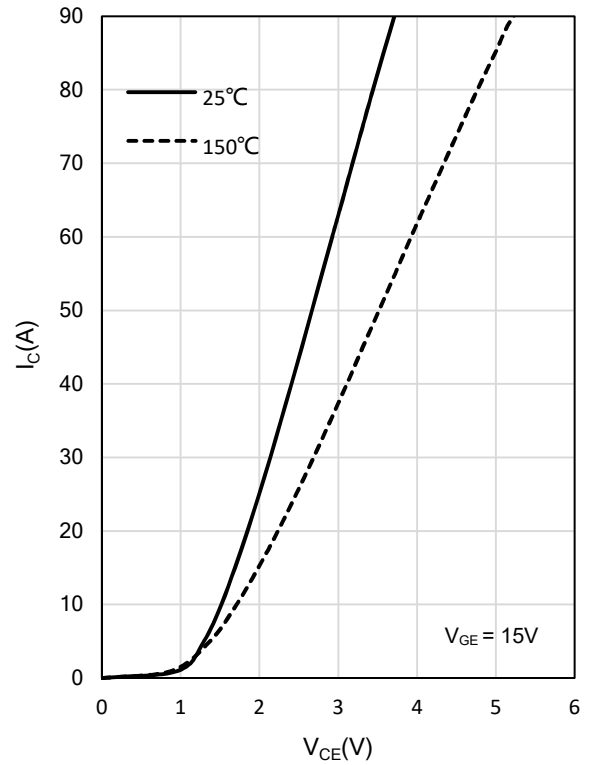




Fig. 5 Turn-off time vs. gate resistor

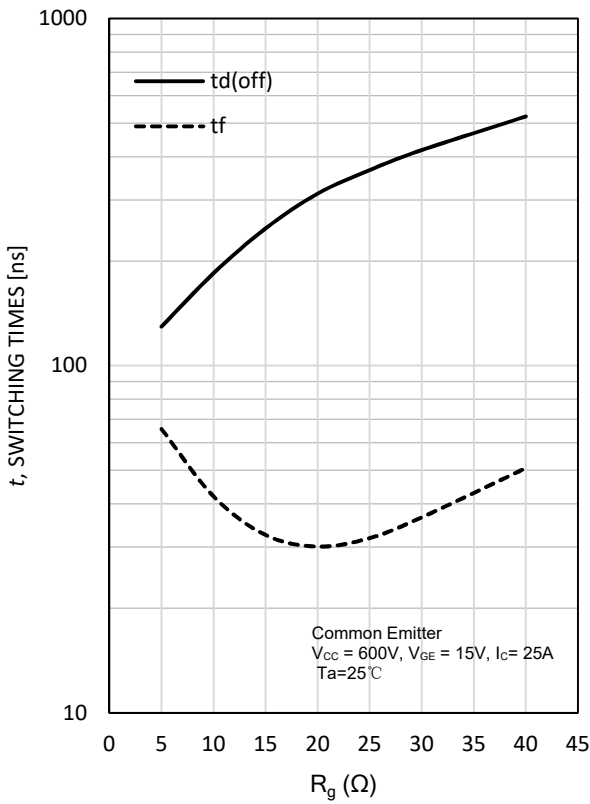


Fig. 6 Turn-off time vs. collector current

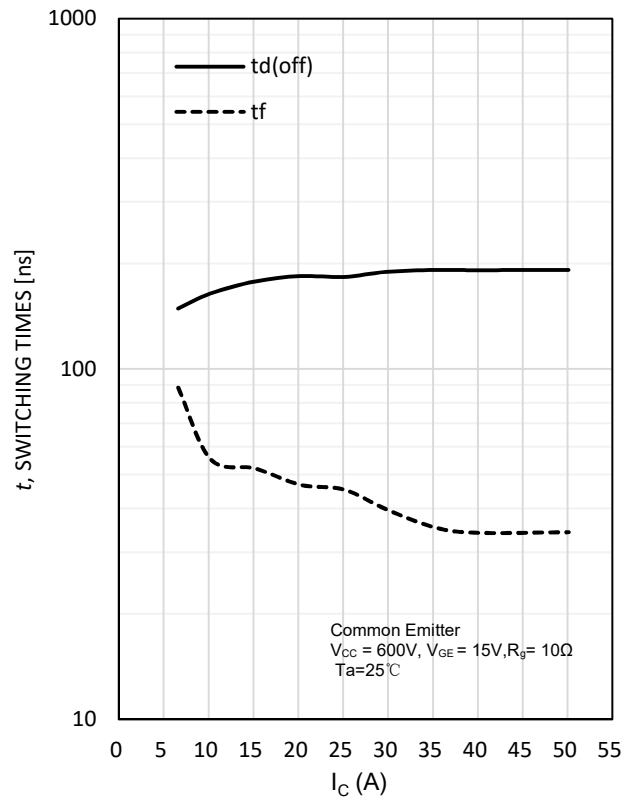


Fig. 7 Switching loss vs. gate resistor

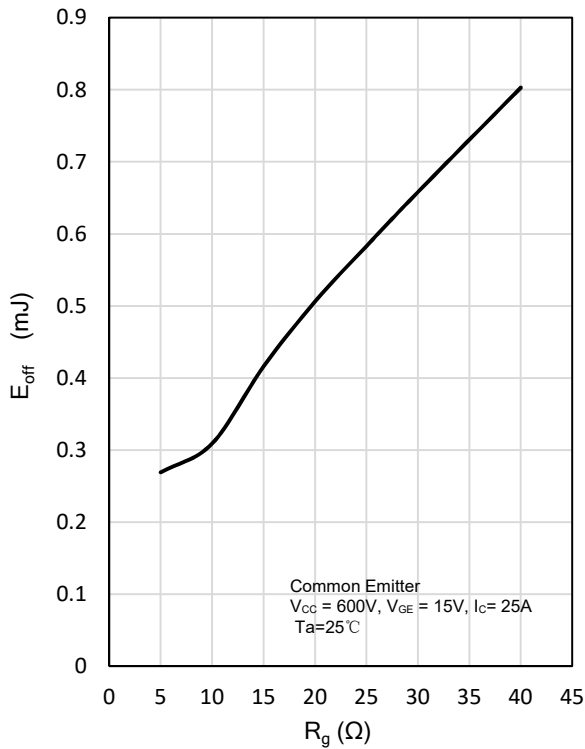


Fig. 8 Switching loss vs. collector current

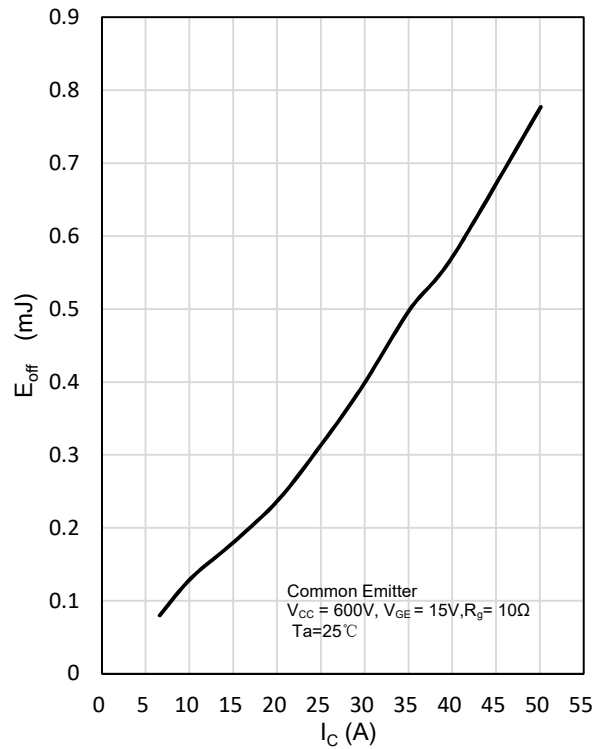




Fig. 9 Gate charge characteristics

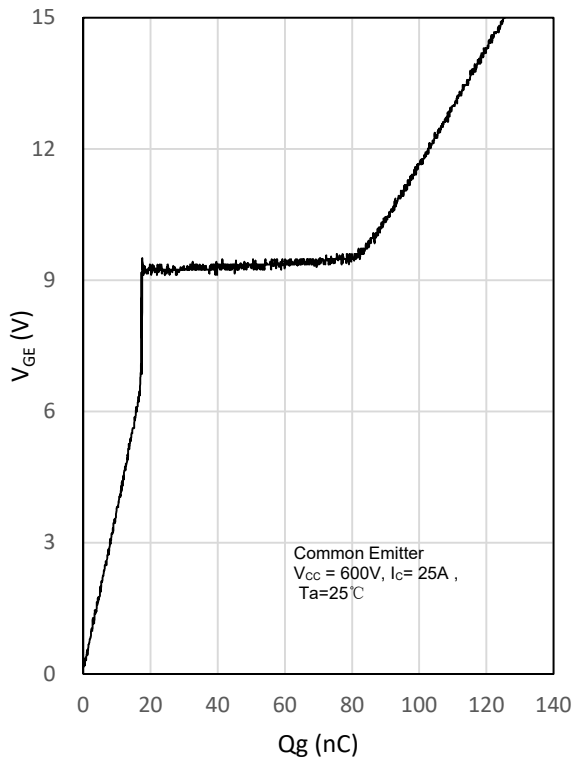
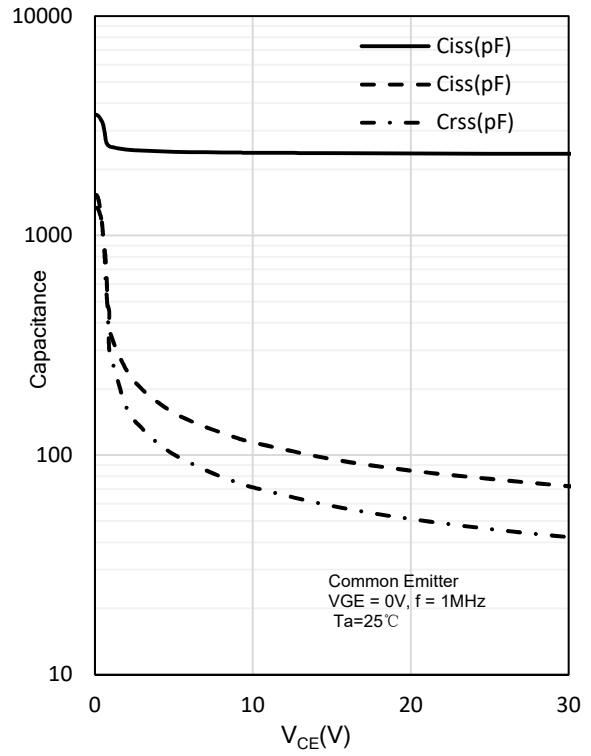
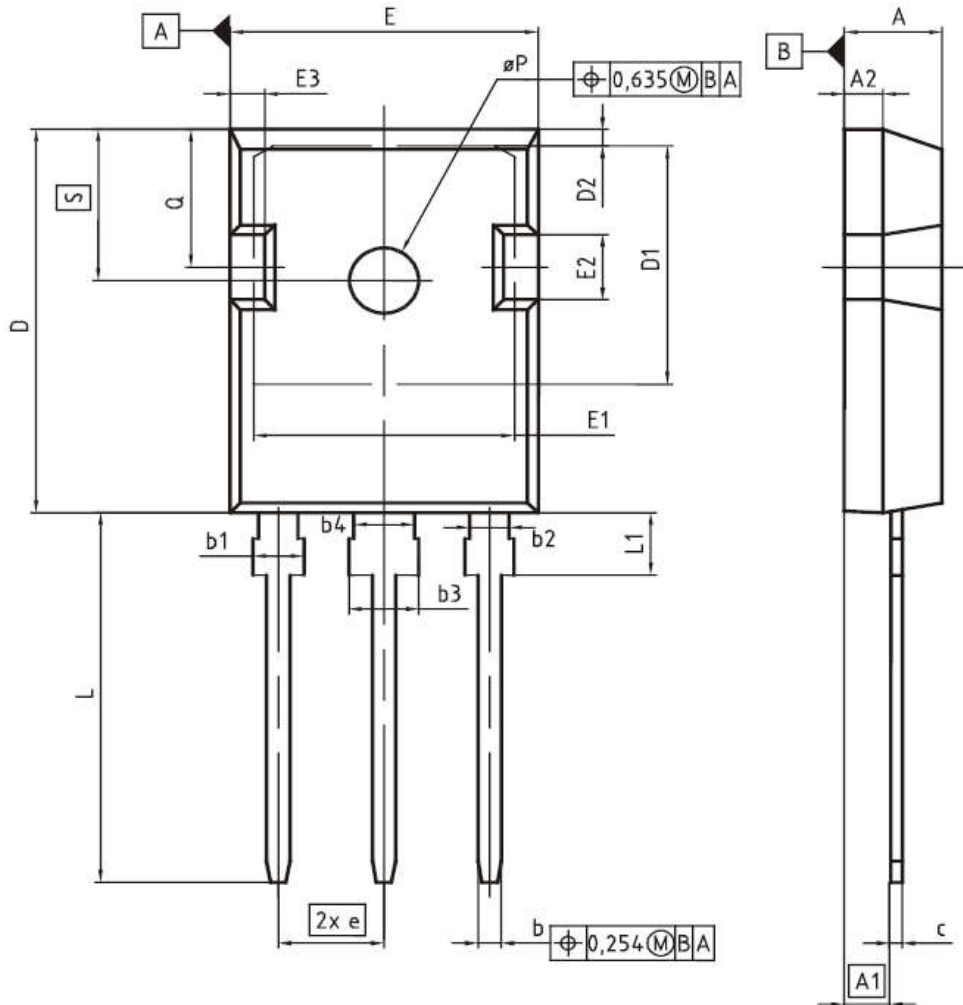


Fig. 10 Capacitance characteristics





PG-TO247-3



| DIM | MILLIMETERS | | INCHES | |
|-----|-------------|-------|-------------|-------|
| | MIN | MAX | MIN | MAX |
| A | 4.83 | 5.21 | 0.190 | 0.205 |
| A1 | 2.27 | 2.54 | 0.089 | 0.100 |
| A2 | 1.85 | 2.16 | 0.073 | 0.085 |
| b | 1.07 | 1.33 | 0.042 | 0.052 |
| b1 | 1.90 | 2.41 | 0.075 | 0.095 |
| b2 | 1.90 | 2.16 | 0.075 | 0.085 |
| b3 | 2.87 | 3.38 | 0.113 | 0.133 |
| b4 | 2.87 | 3.13 | 0.113 | 0.123 |
| c | 0.55 | 0.68 | 0.022 | 0.027 |
| D | 20.80 | 21.10 | 0.819 | 0.831 |
| D1 | 16.25 | 17.65 | 0.640 | 0.695 |
| D2 | 0.95 | 1.35 | 0.037 | 0.053 |
| E | 15.70 | 16.13 | 0.618 | 0.635 |
| E1 | 13.10 | 14.15 | 0.516 | 0.557 |
| E2 | 3.68 | 5.10 | 0.145 | 0.201 |
| E3 | 1.00 | 2.60 | 0.039 | 0.102 |
| e | 5.44 (BSC) | | 0.214 (BSC) | |
| N | 3 | | 3 | |
| L | 19.80 | 20.32 | 0.780 | 0.800 |
| L1 | 4.10 | 4.47 | 0.161 | 0.176 |
| øP | 3.50 | 3.70 | 0.138 | 0.146 |
| Q | 5.49 | 6.00 | 0.216 | 0.236 |
| S | 6.04 | 6.30 | 0.238 | 0.248 |

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